



PTO-1449

INFORMATION DISCLOSURE CITATION
IN AN APPLICATION
(Use several sheets if necessary)

Document Number (Optional)
MEG-03-005

Application Number
10/796,427

Applicant
Mou-Shiung Lin et al.

Filing Date
03/09/04

Group Art Unit

1 of 2

U. S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	PRIOR DATE IF APPROPRIATE
ML	6544880	4/8/03	Akram	438	617	6/14/99
↓	6451681	9/17/02	Greer	438	601	10/4/99
↓	6376353	4/23/02	Zhou et al.	438	612	7/3/00
↓	6495442	12/17/02	Lin et al.	438	618	10/18/00
ML	6383916	5/7/02	Lin	438	637	2/17/99

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Portion(s) Pages, Etc.)

ML	-	US Patent App. MSL-98-002 CCC CIP, Filed 05/24/02, Ser # 10/154,662, assigned to the same assignee, "Top Layers of Metal for High Performance IC's".
ML	-	US Patent App. MEG-02-016, Filed 05/27/03, Ser. # 10/445,558, "High Performance System-on-Chip Inductor Using Post Passivation Process".

EXAMINER

DATE CONSIDERED
8/24/05

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

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[illegible][illegible]

MC	-	U.S. Patent App. Pub. US 2004/0029404 A1 to Lin, Pub Date 2/12/04, Filed 5/27/03, US Cl. 438/958.
MC	-	U.S. Patent App. Pub. US 2004/0016948 A1 to Lin, Pub. Date 1/29/04, Filed 5/27/03, US Cl. 257,300.

DATE CONSIDERED

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